

10/508745  
DT04 Rec'd PCT/PTO 21 SEP 2004

**Amendments to the Claims**

1. (*Original*) A semiconductor device comprising a substrate with a first and an opposed second side, at which first side a plurality of transistors and interconnects is present, which are covered by a protective security covering, which device is further provided with bond pad regions, characterized in that the protective security covering comprises a substantially non-transparent and substantially chemically inert security coating, and the bond pad regions are accessible from the second side of the substrate.

2. (*Currently Amended*) A semiconductor device as claimed in Claim 1, characterized in that

[[ - ]] the bond pad regions are present on the first side of the substrate, and

[[ - ]] the substrate is a silicon substrate, that is patterned as required for access to the bond pad regions.

3. (*Currently Amended*) A semiconductor device as claimed in Claim 1, ~~as claimed in Claim 1 or 2~~, characterized in that a security layer is present at the second side of the substrate, which security layer leaves exposed the bond pad regions or any metallisation for access thereto.

4. (*Original*) A semiconductor device as claimed in Claim 1, characterized in that the bond pad regions protected against probing with antiprobe means.

5. (*Currently Amended*) A semiconductor device as claimed in Claim 1, characterized in that the security coating comprises a layer of TiO<sub>2</sub>, ~~comprises a layer of TiO<sub>2</sub>~~.

6. (*Original*) A semiconductor device as claimed in Claim 1, characterized in that the security coating is formed of multiple alternate layers, which alternate layers are sensitive to different etchants.

7. (*Original*) A carrier comprising a semiconductor device according to Claim 1.

8. (*Currently Amended*) A method of manufacturing a semiconductor device provided with a substrate with a first and second side, comprising the steps of:

[[ - ]] providing a structure of transistors and interconnects at the first side of the substrate, the structure including bond pad regions that are defined at an interface with the substrate;

[[ - ]] applying a protective security covering including at least a substantially non-transparent and substantially chemically inert security coating;

[[ - ]] patterning the substrate from the second side so as to expose the bond pad regions.

9. (*Original*) A method according to Claim 8, wherein the substrate is a semiconductor substrate that is thinned and etched to expose the bond pad regions.

10. (*Currently Amended*) A method according to Claim 8, ~~Claim 8 or 9~~, wherein a second substrate is provided on the protective security covering and attached to it by means of glue.